formation of the first and second layers being at least 500°C, and the first layer being formed so as to contain an amount of the element equal to one of zero and an amount less than the amount of the element contained in the second layer; and

cooling from the formation temperature at least to 450°C with a cooling speed of at least 30°C/minute.

REMARKS

Claims 24-28 and 61-83 are presented for examination. Claims 24, 25, 73 and 83 are in independent form. Claims 27 and 28 have been amended to define more clearly what Applicants regard as their invention. Support for the changes can be found in the original application as filed. Therefore, no new matter has been added.

Applicants request early and favorable examination on the merits.

Applicants' undersigned attorney may be reached in our Washington, D.C. Office by telephone at (202) 530-1010. All correspondence should continue to be directed to our below listed address.

Respectfully submitted,

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APPENDIX

VERSION SHOWING CHANGES MADE TO CLAIMS

27. (Twice Amended) A method for manufacturing a liquid discharge recording head according to Claim 24, wherein [a silicon substrate is used as the substrate, and in said step of forming the pressure chambers the substrate is partially removed] the piezoelectric film is processed by etching using a [mixed] strong acid solution [of hydrochloric acid and nitric acid to form the pressure chambers in the interior of the substrate].

28. (Twice Amended) A method for manufacturing a liquid discharge recording head according to Claim [27] 24, wherein [in said step of forming the pressure chambers the] a silicon substrate is [partially] used as the substrate, and the substrate is removed by etching using hydrofluoric acid solution or potassium hydroxide solution to form the pressure chambers therein.